

ABSTRACT OF THE DISCLOSURE

An ohmic electrode for an SiC semiconductor includes a p-type Si layer formed on the surface of a p-type SiC semiconductor, and a metal silicide layer formed on the surface of the Si layer, the metal silicide layer being formed from a metal silicide such as PtSi. The p-type Si layer is preferably formed from p-type Si having a carrier concentration equal to or higher than that of the aforementioned p-type SiC. Preferably, the ohmic electrode is formed as follows: deposition of Si is performed; deposition of a metal silicide is performed by means of laser ablation; laser irradiation is performed to thereby improve ohmic properties and enhance adhesion between the resultant deposition layer and the p-type SiC semiconductor; and then further deposition of the metal silicide is performed by means of laser ablation.